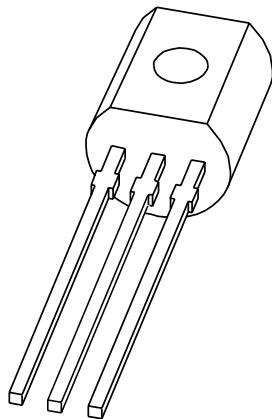


DATA SHEET



BF199

NPN medium frequency transistor

Product specification
Supersedes data of 1997 Jul 07

2004 Nov 08

NPN medium frequency transistor

BF199

FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 25 V).

APPLICATIONS

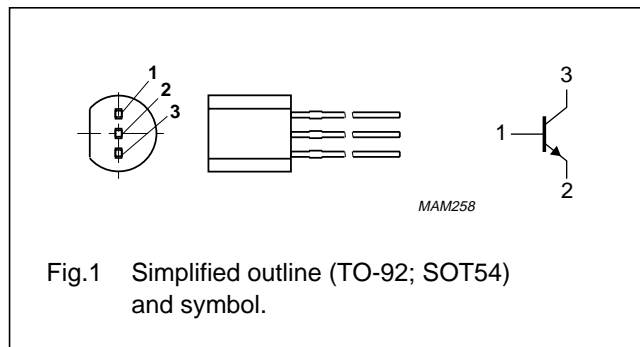
- Output stage of a vision IF amplifier.

DESCRIPTION

NPN medium frequency transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	–	25	V
I_{CM}	peak collector current		–	–	25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	–	500	mW
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}; I_C = 7\text{ mA}$	38	–	–	
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 5\text{ mA}; f = 100\text{ MHz}$	–	550	–	MHz

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF199	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

NPN medium frequency transistor

BF199

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	25	V
V_{EBO}	emitter-base voltage	open collector	–	4	V
I_C	collector current (DC)		–	25	mA
I_{CM}	peak collector current		–	25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}$; $I_E = 0\text{ A}$	–	–	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}$; $I_C = 0\text{ A}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}$; $I_C = 7\text{ mA}$	38	–	–	
V_{BE}	base-emitter voltage	$V_{CE} = 10\text{ V}$; $I_C = 7\text{ mA}$	–	775	925	mV
C_{re}	feedback capacitance	$V_{CB} = 10\text{ V}$; $I_C = 0\text{ A}$; $f = 1\text{ MHz}$	–	–	0.5	pF
f_T	transition frequency	$V_{CE} = 10\text{ V}$; $I_C = 5\text{ mA}$; $f = 100\text{ MHz}$	–	550	–	MHz

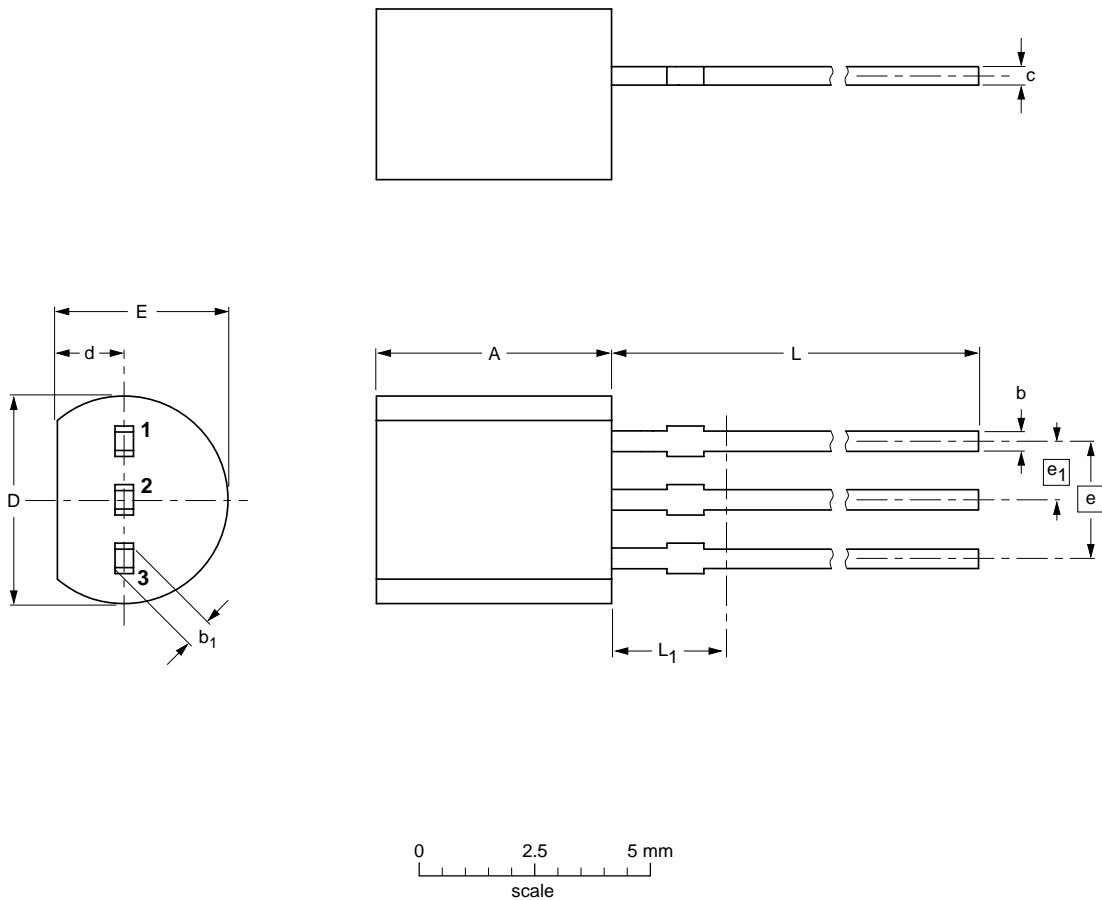
NPN medium frequency transistor

BF199

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		-97-02-28 04-06-28

NPN medium frequency transistor

BF199

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Printed in The Netherlands

R75/03/pp6

Date of release: 2004 Nov 08

Document order number: 9397 750 13577

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